TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (Ultra-High-Speed U-MOSIII)

TPCA8020-H

High-Efficiency DC ∕ DC Converter Applications Notebook PC Applications

Portable Equipment Applications
CCFL Inverter Applications

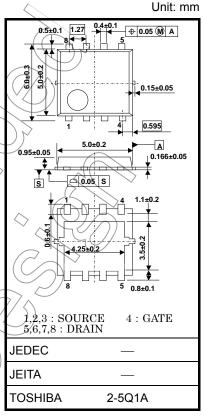
- Small footprint due to a small and thin package
- High speed switching
- Small gate charge: Qsw = 3.5 nC (typ.)

Low drain-source ON-resistance: RDS (ON) = 22 m Ω (typ.)

- $\bullet~$ High forward transfer admittance: $|\,Y_{fs}\,|\,$ = 15 S (typ.)
- Low leakage current: $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 40 \text{ V)}$
- Enhancement mode: $V_{th} = 1.1$ to 2.3 V ($V_{DS} = 10$ V, $I_D = 1$ mA)

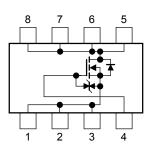
Absolute Maximum Ratings (Ta = 25°C)

| Characteristic | | | Symbol | Rating | Unit | |
|--|-------|----------|--------------------|------------|--|--|
| Drain-source voltage | | | V_{DSS} | 40 | V | |
| Drain-gate voltage (R_{GS} = 20 k Ω) | | | V _{DGR} < | 40 | /X | |
| Gate-source voltage | | | V _{GSS} | ±20 | \\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\ | |
| Drain current | DC | (Note 1) | I _D (| 7.5 | A | |
| | Pulse | (Note 1) | | 30 | ^ | |
| Drain power dissipation (Tc=25° C) | | | (P_D) | 30 _ | //w | |
| Drain power dissipation (t = 10 s) (Note 2a) | | | PD | 2.8 | MA | |
| Drain power dissipation (Note 2b) | | | PD | (1.6/ | W | |
| Single-pulse avalanche energy (Note 3) | | | EAS | 26 | mJ | |
| Avalanche current | | | I _{AR} | 7.5 | Α | |
| Repetitive avalanche energy Single-device value at dual operation (Note 2a, 4) | | | EAR | 1.9 | mJ | |
| Channel temperature | | | Toh | 150 | °C | |
| Storage temperature range | | | T _{st9} | -55 to 150 | °C | |



Weight: 0.066 g (typ.)

Circuit Configuration



Note: For Notes 1 to 4, refer to the next page.

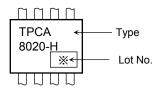
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care.

Thermal Characteristics

| Characteristic | Symbol | Max | Unit |
|---|------------------------|------|------|
| Thermal resistance, channel to case $\mbox{(Tc=25$^{\circ}$ C)}$ | R _{th (ch-c)} | 4.17 | °C/W |
| Thermal resistance, channel to ambient $(t = 10 \text{ s})$ (Note 2a) | R _{th (ch-a)} | 44.6 | °C/W |
| Thermal resistance, channel to ambient (t = 10 s) (Note 2b) | R _{th (ch-a)} | 78.1 | °C/W |

Marking (Note 5)



Note 1: The channel temperature should not exceed 150°C during use.

Note 2:

a) Device mounted on a glass-epoxy board (a)

Device mounted on a glass-epoxy board (b)



Note 3: $V_{DD} = 24 \text{ V}$, $T_{Ch} = 25^{\circ}\text{C}$ (initial), L = 0.5 mH, $R_{G} = 25 \Omega$, $I_{AR} = 7.5 \text{ A}$

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: * Weekly code: (Three digits)

Week of manufacture

(01 for first week of the year, continuing up to 52 or 53)

2

Year of manufacture

(The last digit of the calendar year)

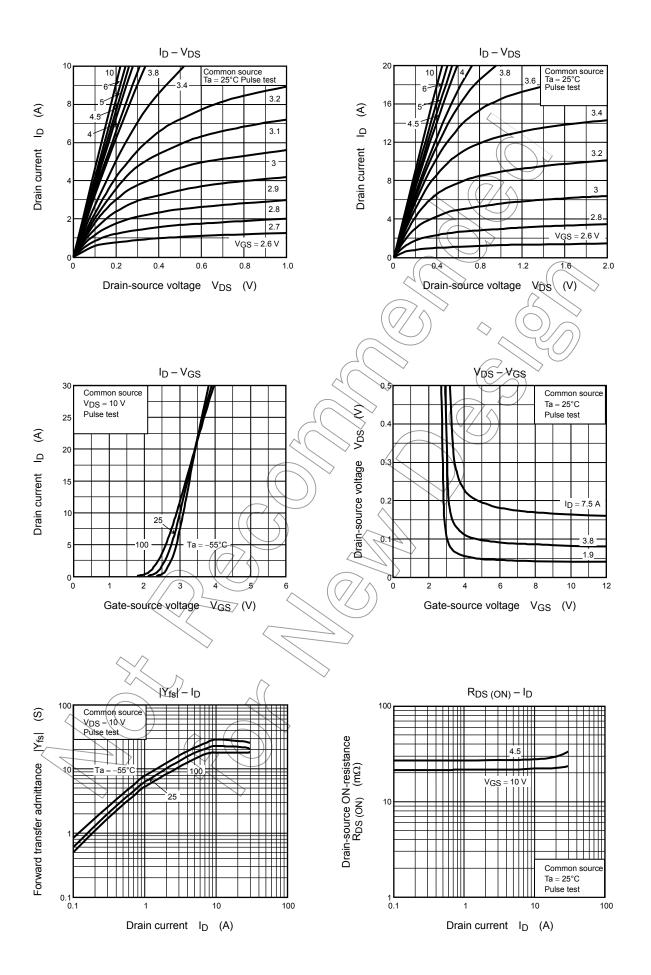
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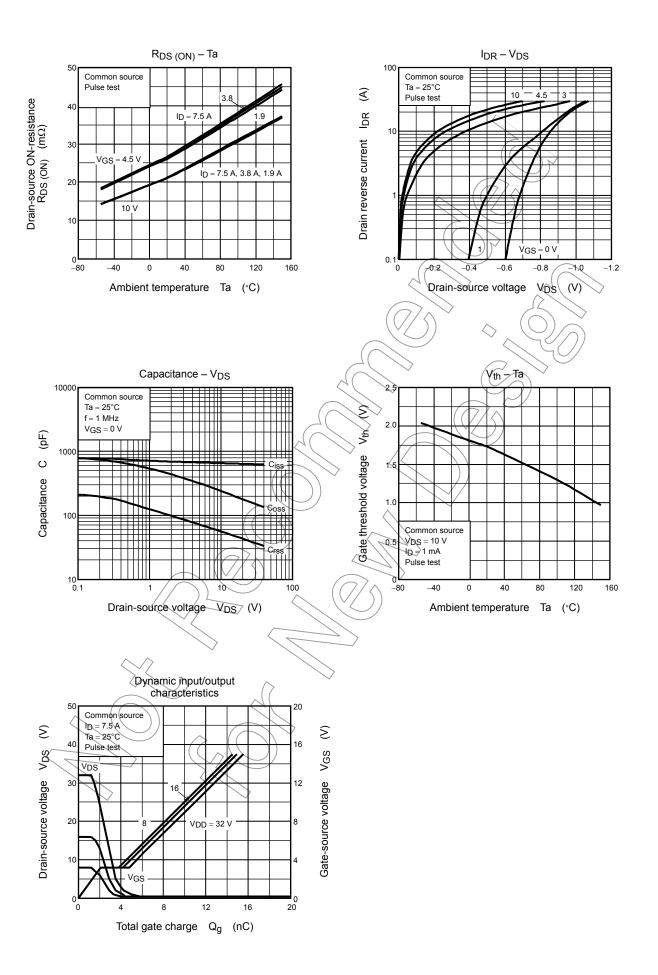
Electrical Characteristics (Ta = 25°C)

| Characteristic | | Symbol | Test Condition | Min | Тур. | Max | Unit |
|---|---------------|-----------------------|---|---------------|------|--------|--------|
| Gate leakage current | | I _{GSS} | V _{GS} = ±16 V, V _{DS} = 0 V | _ | _ | ±10 | μА |
| Drain cutoff curi | rent | I _{DSS} | V _{DS} = 40 V, V _{GS} = 0 V | _ | _ | 10 | μА |
| Drain-source breakdown voltage | | V _{(BR) DSS} | I _D = 10 mA, V _{GS} = 0 V | 40 | | 1 | V |
| | | V _{(BR) DSX} | I_D = 10 mA, V_{GS} = -20 V | 25 | _ | | V |
| Gate threshold voltage | | V_{th} | V _{DS} = 10 V, I _D = 1 mA | 7 |) > | 2.3 | > |
| Drain-source ON-resistance | | R _{DS} (ON) | V _{GS} = 4.5 V, I _D = 3.8 A | \nearrow | 27 | 35 | mΩ |
| | | R _{DS (ON)} | V _{GS} = 10 V, I _D = 3.8 A | \rightarrow | 22 | 27 | 1112.2 |
| Forward transfer admittance | | Y _{fs} | V _{DS} = 10 V, I _D = 3.8 A | 7.5 | 15 | | S |
| Input capacitance | | C _{iss} | | | 650 | | |
| Reverse transfer capacitance | | C _{rss} | V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz | | 55 | 1 | pF |
| Output capacitance | | Coss | | | 240 | \vee | |
| Switching time | Rise time | tr | V _{GS} 10 V I _D = 3.8 A V _{OUT} C _S v _O V _{OUT} | | 3 | > | ns |
| | Turn-on time | t _{on} | | | | _ | |
| | Fall time | t _f | V _{DD} ≈ 20 V | | 2 | | 115 |
| | Turn-off time | t _{off} | Duty ≦ 1%, t _w = 10 μs | <i>)</i> _ | 18 | | |
| Total gate charge (gate-source plus gate-drain) | | Q_g (| $V_{DD} = 32 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 7.5 \text{ A}$ | | 11 | | |
| | | | $V_{DD} = 32 \text{ V}, V_{GS} = 5 \text{ V}, I_D = 7.5 \text{ A}$ | | 6.2 | | |
| Gate-source charge | | Q _{gs1} | \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ | _ | 2.1 | _ | nC |
| Gate-drain ("Miller") charge | | Qgd | $V_{DD} \simeq 32 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 7.5 \text{ A}$ | | 2.7 | | |
| Gate switching charge | | Qsw | | _ | 3.5 | _ | |

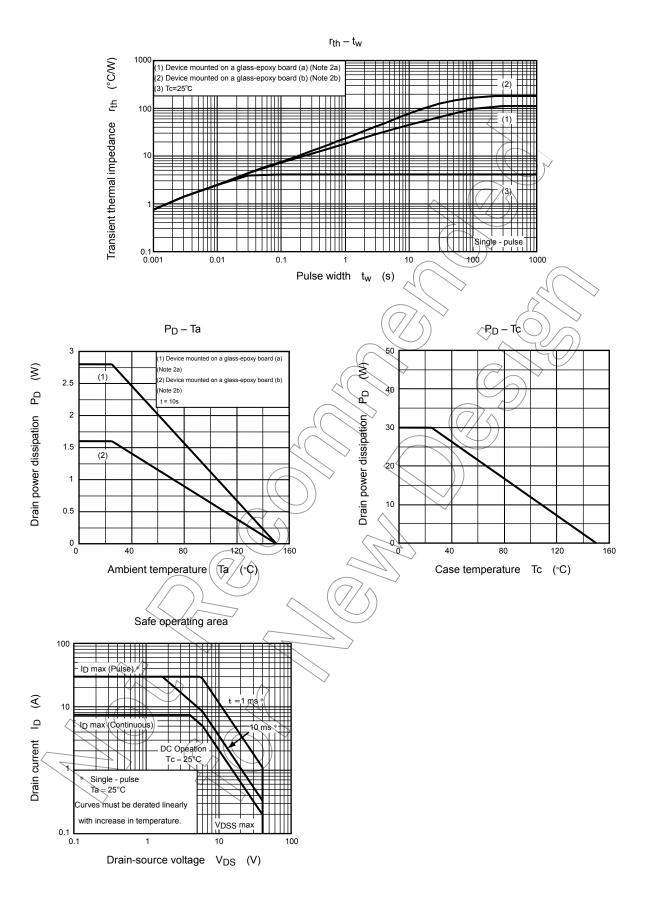
Source-Drain Ratings and Characteristics (Ta = 25°C)

| Characteristic Symbol Test Condition | Min | Тур. | Max | Unit |
|--|-----|------|------|------|
| Drain reverse current Pulse (Note 1) I _{DRP} — | _ | _ | 30 | Α |
| Forward voltage (diode) V _{DSF} (I _{DR} = 7.5 A, V _{GS} = 0 V | _ | _ | -1.2 | V |





5 2006-11-17



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